

BE-III/6(B)

2000/10  
212654

(I.T. Engg.)

**BASIC ELECTRONICS—COURSE NO. ECE-313**

Time Allowed—3 Hours

Maximum Marks—100

Note :— Attempt five questions in all, by selecting at least one question from each Unit. All questions carry equal marks.

**Unit I**

1. (a) Explain in detail Zener diode and its break-down phenomenon in detail with neat diagram. 10

- (b) Explain with neat diagram the working of LED, photodiode and varactor diode. 10

Or

2. (a) Explain and derive an expression for  $I_{avg}$ ,  $V_{avg}$ ,  $I_{rms}$ ,  $V_{rms}$ , ripple factor, TUF, PIV,  $\eta$  in case of full wave bridge rectifier with neat diagram. 12

- (b) The reverse current of Si diode is found to be 50 nA at 27°C with 10 V reverse voltage. The junction temp. was observed to rise upto 105°C. Calculate the maximum value of reverse current at temp. 105°C. 8

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## Unit II

3. (a) Explain with neat diagram the working of transistor in common collector configuration and draw the I/P and O/P characteristics. Show the active, saturation and cut-off region. How characteristics can be modified by early effect ?

12

- (b) A p-n-p transistor has  $\beta = 50$   $I_{CO} = 2 \mu \text{ Amp}$ . A C.E. configuration is used with  $V_{CC} = -12 \text{ V}$  and  $R_C = 4 \text{ k}\Omega$ . What is the minimum  $I_B$  required to saturate the transistor shown in Fig. 1. Use  $V_{CE(sat)} = -0.2 \text{ V}$

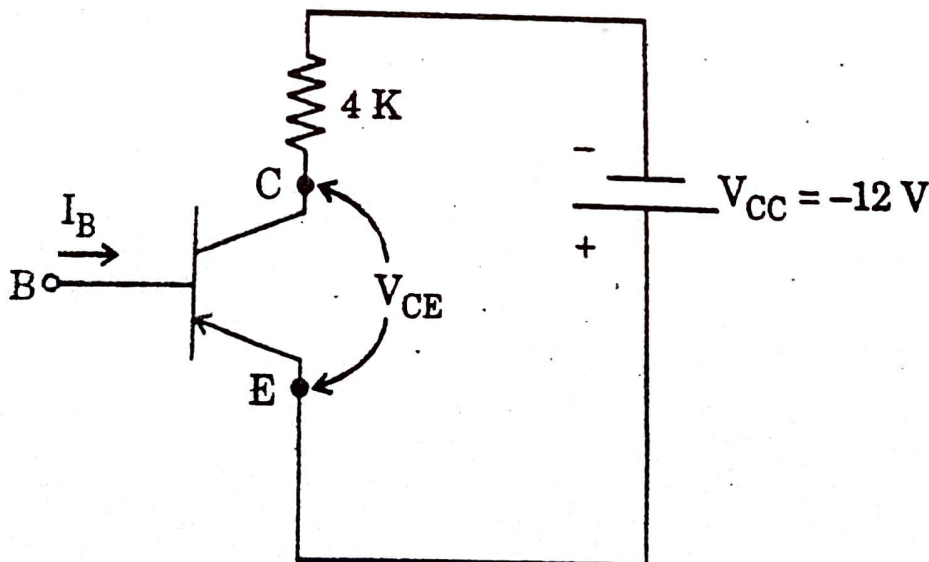


Fig. 1



Or

4. (a) Explain the concept of thermal runaway in transistors.  
Also explain the Bias compensation technique for compensation of  $I_{CO}$ . 10
- (b) Explain in detail the transistor components. Also write the Generalized Transistor Equation. 10

### Unit III

5. (a) Draw and explain the JFET small signal model and write equation. 5
- (b) Draw the low frequency model of JFET in C.S. configuration and derive the expression for  $A_v$ ,  $R_i$ ,  $R_o$  with and without  $R_s$ . 15

Or

6. (a) Explain with neat diagram, working of depletion MOSFET.  
Draw symbol, characteristics. 10

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- (b) A C.S. FET amplifier with unbypassed  $R_s$  has the following parameters :

$$R_d = 15 \text{ k}\Omega, R_s = 0.5 \text{ k}\Omega, R_g = 1 \text{ M}\Omega, r_d = 5 \text{ k}\Omega,$$

$$g_m = 5 \text{ mS}, V_{DD} = 20 \text{ V. Calculate } A_v, R_i, R_o. \text{ Draw the}$$

load line also.

10

#### Unit IV

7. (a) Explain the working of op-amp as voltage follower and inverter. Draw the I/P and O/P waveform in each case.

10

- (b) Explain the working of op-amp as summing, scaling and average amplifier in case of N. Inv. amplifier.

10

Or

8. (a) Explain the working of op-amp as voltage limiters and comparators.

10

- (b) Explain the working of op-amp as integrator and differentiator.

10